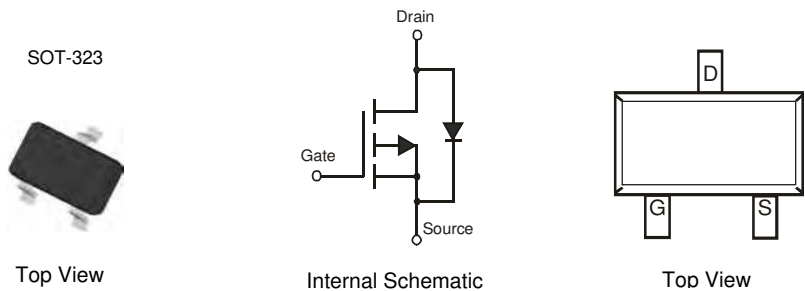


Features

- P-Channel MOSFET
- Low On-Resistance
 - 150 mΩ @ $V_{GS} = -4.5V$
 - 200 mΩ @ $V_{GS} = -2.5V$
 - 240 mΩ @ $V_{GS} = -1.8V$
- Very Low Gate Threshold Voltage $V_{GS(th)} \leq 1V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Lead Free By Design/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3)**
- **Qualified to AEC-Q101 standards for High Reliability**

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish — Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.006 grams (approximate)



Maximum Ratings @ $T_A = 25^\circ C$ unless otherwise specified

Characteristic	Symbol	Value	Units	
Drain-Source Voltage	V_{DSS}	-20	V	
Gate-Source Voltage	V_{GSS}	± 12	V	
Drain Current (Note 1)		$T_A = 25^\circ C$	-1.5	A
		$T_A = 70^\circ C$	-1.0	A
Pulsed Drain Current	I_{DM}	-5	A	

Thermal Characteristics

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	P_D	250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	500	$^\circ C/W$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ C$

- Notes:
1. Device mounted on FR-4 substrate PC board, 2oz. Copper, with minimum recommended pad layout.
 2. No purposefully added lead.
 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0 -5.0	μA	T _J = 25°C T _J = 125°C V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±12V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.45	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	92	150	mΩ	V _{GS} = -4.5V, I _D = -2.0A
			134	200		
			180	240		
Forward Transconductance	g _{FS}	—	3.1	—	S	V _{DS} = -10V, I _D = -810mA
Diode Forward Voltage (Note 4)	V _{SD}	—	—	-0.9	V	V _{GS} = 0V, I _S = -0.5A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	—	320	—	pF	V _{DS} = -16V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	80	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	60	—	pF	
Turn-On Delay Time	t _{D(on)}	—	12.5	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _L = 10Ω, R _G = 1.0Ω
Turn-On Rise Time	t _r	—	10.3	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	46.5	—	ns	
Turn-Off Fall Time	t _f	—	22.2	—	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.

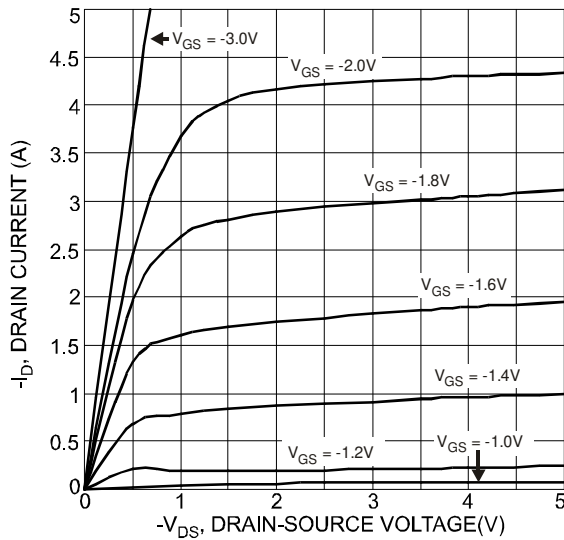


Fig. 1 Typical Output Characteristics

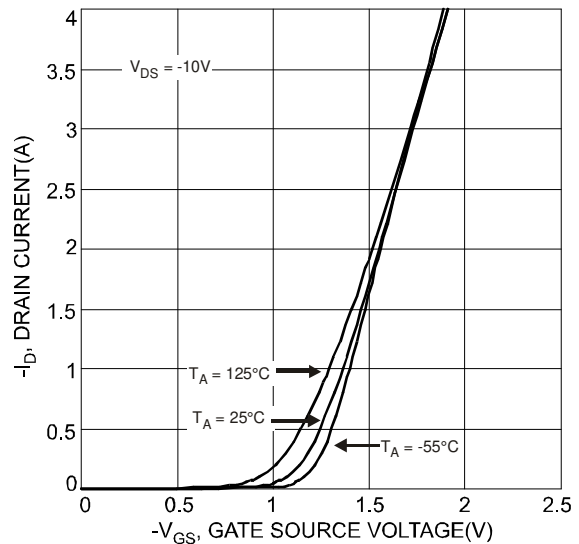


Fig. 2 Typical Transfer Characteristics

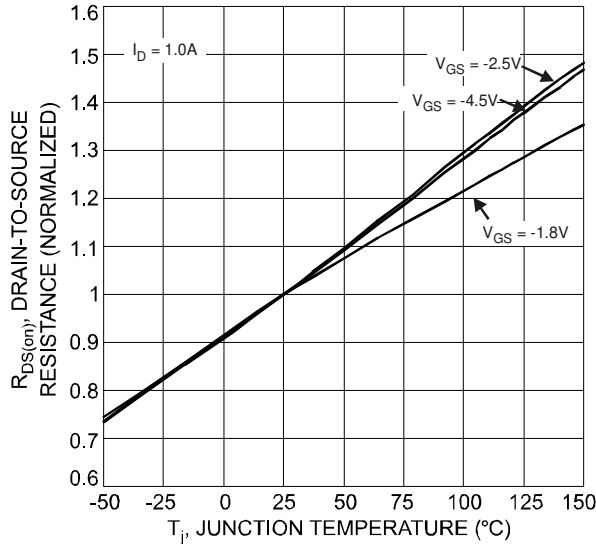


Fig. 3 On-Resistance Variation with Temperature

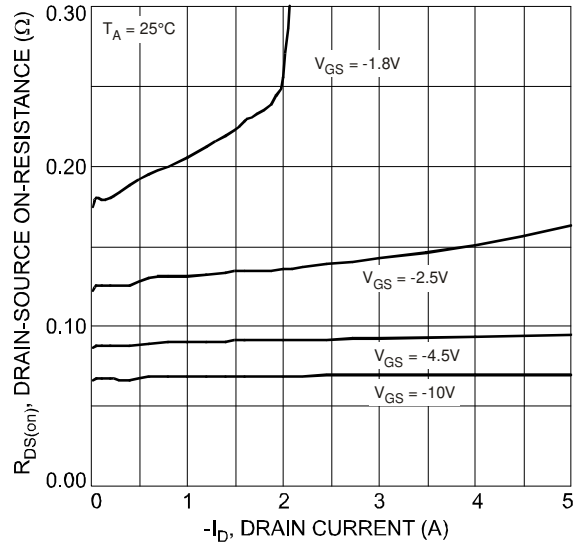


Fig. 4 On-Resistance vs Drain Current and Gate Voltage

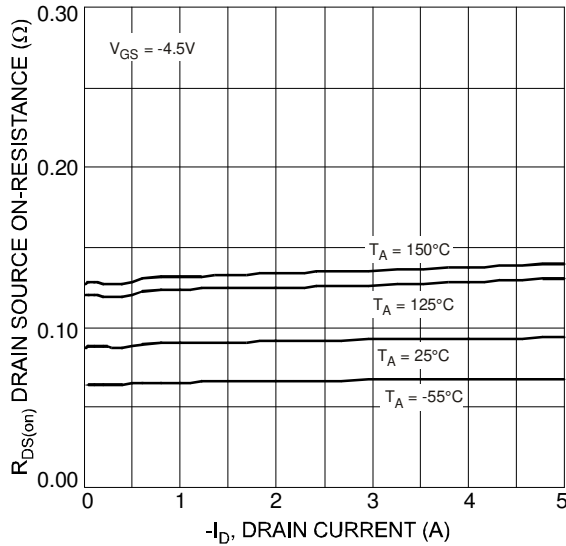


Fig. 5 Drain-Source On-Resistance Vs. Drain Current and Temperature

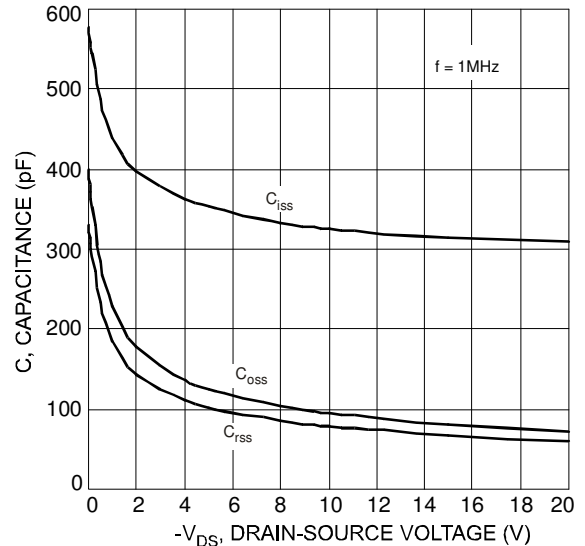


Fig. 6: Typical Capacitance

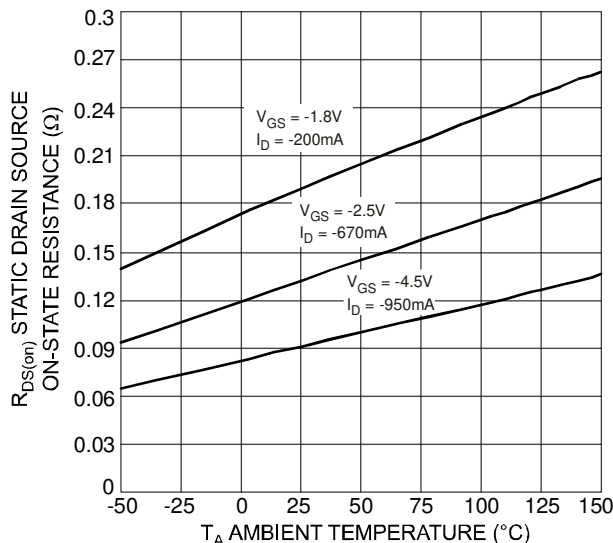


Fig. 7 Static Drain-Source On-State Resistance vs Ambient Temperature

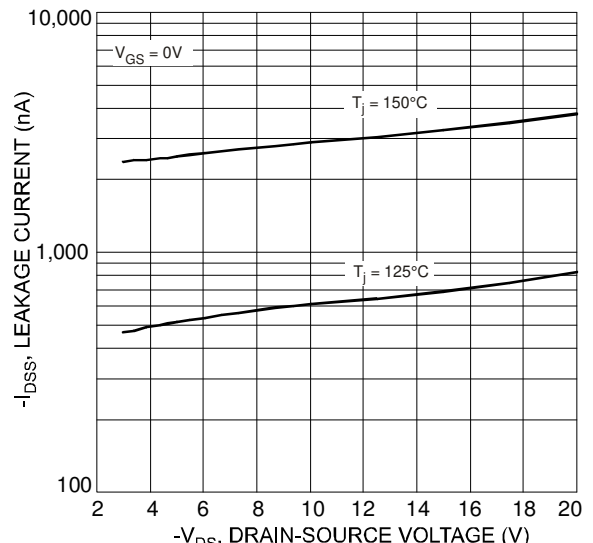


Fig. 8 Drain-Source Leakage Current vs Voltage

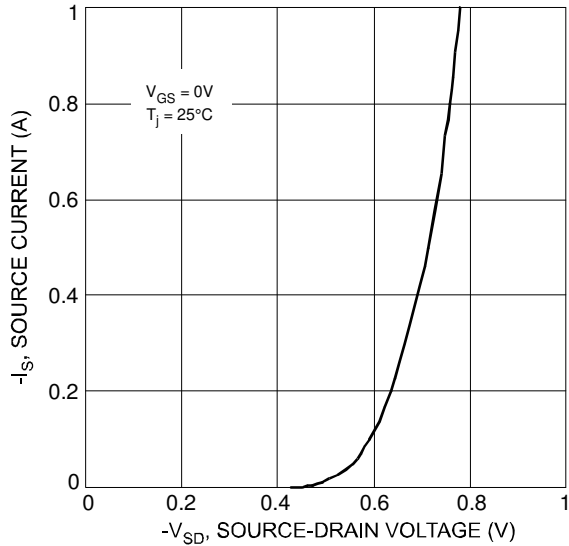


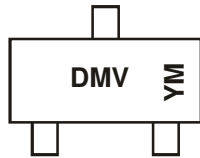
Fig. 9 Diode Forward Voltage vs. Current

Ordering Information (Note 5)

Part Number	Case	Packaging
DMP2240UW-7	SOT-323	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



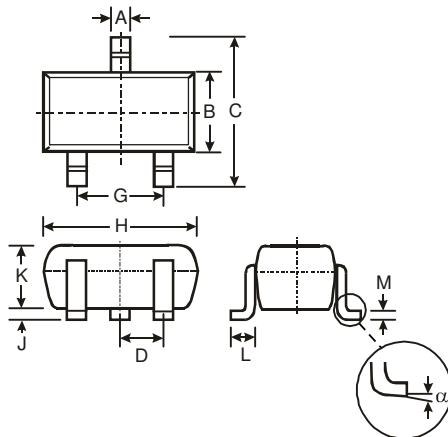
DMV = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: V = 2008)
 M = Month (ex: 9 = September)

Date Code Key

Year	2008	2009	2010	2011	2012	2013	2014	2015
Code	V	W	X	Y	Z	A	B	C

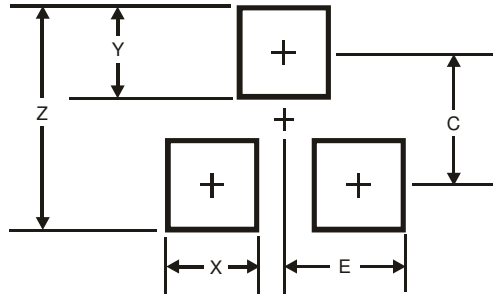
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Package Outline Dimensions



SOT-323			
Dim	Min	Max	Typ
A	0.25	0.40	0.30
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	-	-	0.65
G	1.20	1.40	1.30
H	1.80	2.20	2.15
J	0.0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
X	0.7
Y	0.9
C	1.9
E	1.0

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